

BCW61A**PNP EPITAXIAL SILICON TRANSISTOR**

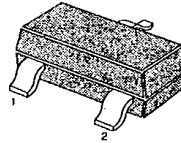
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GENERAL PURPOSE TRANSISTOR**ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	32	V
Collector-Emitter Voltage	V_{CE0}	32	V
Emitter-Base Voltage	V_{EB0}	5.0	V
Collector Current	I_C	100	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$

• Refer to MMBT5086 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=2\text{mA}, I_B=0$	32		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1\mu\text{A}, I_C=0$	5		V
Collector Cutoff Current	I_{CES}	$V_{CE}=32\text{V}, V_{BE}=0$		20	nA
DC Current Gain	h_{FE}	$V_{CE}=5\text{V}, I_C=2\text{mA}$	120	220	
		$V_{CE}=1\text{V}, I_C=50\text{mA}$	60		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=0.25\text{mA}$		0.25	V
		$I_C=50\text{mA}, I_B=1.25\text{mA}$		0.55	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=0.25\text{mA}$	0.6	0.85	V
		$I_C=50\text{mA}, I_B=1.25\text{mA}$	0.68	1.05	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=2\text{mA}, V_{CE}=5\text{V}$	0.6	0.75	V
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0$ $f=1\text{MHz}$		6	pF
Noise Figure	NF	$I_C=0.2\text{mA}, V_{CE}=5\text{V}$ $R_S=2\text{K}\Omega, f=1\text{KHz}$		6	dB
Turn On Time	t_{on}	$I_C=10\text{mA}, I_{B1}=1\text{mA}$		150	ns
Turn Off Time	t_{off}	$I_{B2}=1\text{mA}, V_{BB}=3.6\text{V}$ $R_L=990\Omega$		800	ns

Marking

